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09/511,502

APPLICANT

Tatau NISHINAGA

FILING DATE

February 23, 2000

GROUP

4765-1720

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
F.H.	6 3 9 9 4 7 3	06/2002	Fischer et al.	—	—	—
F.H.	4 1 7 1 2 3 4	10/1979	Nagata et al.	—	—	—

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES NO
6 1 2 7 1 8 1 7	12/1986	JP	—	—	Abstract
1 9 7 2 9 1 8 6	01/1999	DE	—	—	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

F.H.	German Office Action dated June 21, 2004 with English translation.
F.H.	H. GOSSNER, et al.; "Self-Organizing Growth of Nanometer Mesa Structures on Silicon (100) Substrates", Jpn. J. Appln. Phys. Vol. 33 (1994) pp. 2268-2271, Part 1, No. 4B, April 1994.
F.H.	B-Y. TSAUR, et al.; "Low-dislocation-density GaAs epilayers grown on Ge-coated Si substrates by means of lateral epitaxial overgrowth", Appln. Phys. Lett. 41(4), 15 August 1982, pp. 347-349.
F.H.	Y. MATSUNAGA, et al.; "Microchannel Epitaxy of GaAs ON Si(100) Substrates Using SiO ₂ Shadow Masks", Electrochemical Society Proceedings Volume 97-21 (1997), pp. 184-188.

EXAMINER

Libertine

DATE CONSIDERED

3/23/2006

EXAMINER: Initial if citation is considered, draw line through citation if not in conformance and not considered.
Include copy of this form with next communication to applicant.